

uniformizing the light to be applied in such a manner that the intensity of said light in a predetermined area on the photo mask distributes within a range of  $\pm 11.2\%$  of the average intensity of said light in said area,

wherein spatial distribution of peak intensity of light projected and applied on the semiconductor thin film is uniformized to an identical extent with the peak intensity of the intensity distribution on the photo mask.

17. (Amended) The method according to claim 1, wherein said projected light comprises a laser beam.

18. (Amended) The method according to claim 17, wherein said laser beam is generated by an eximer laser.

19. (Amended) The method according to claim 17, wherein said light is uniformized using a homogenizer, a mask and a projection lens through which said light is applied.

20. (Amended) The method according to claim 19, wherein said mask includes a slit for throttling light passed through the homogenizer into a rectangular beam.

21. (Amended) A method according to claim 19, wherein a projection lens is used for reducing and projecting a slit image of the mask onto said film.

22. (Amended) A semiconductor thin film forming method comprising:  
modifying a predetermined region of a semiconductor thin film by exposing the semiconductor thin film to a projected light patterned through plural patterns formed on a photo mask,

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